Abstracts

New extraction method for FET extrinsic capacitances using active bias conditions

F. Lenk and R. Doerner. "New extraction method for FET extrinsic capacitances using active bias conditions." 1998 MTT-S International Microwave Symposium Digest 98.1 (1998 Vol. I [MWSYM]): 279-282.

A new procedure for extracting the extrinsic capacitances of FETs is presented. It requires measurements only in the active bias regime. The method utilizes the symmetry of the intrinsic FET in the forward and reverse biased operating regime. The extraction is performed analytically and does not require any optimization.

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